
Contents

1	Introduction	1
2	Fundamentals	5
2.1	Point-to-Point Versus Point-to-Multipoint Access	5
2.1.1	Point-to-Point Access	5
2.1.2	Point-to-Multipoint Access	6
2.2	Continuous-Mode Versus Burst-Mode Communication	7
2.2.1	Continuous-Mode Communication	7
2.2.2	Burst-Mode Communication	7
2.3	Components of the Optical Receiver Front-End	8
2.4	Optical Fibers	9
3	Photodetectors	13
3.1	Basics of Photodetectors	13
3.2	Avalanche Photodiode	18
3.3	Pin Photodiode	18
3.4	SiGe Photodetectors	19
3.4.1	Heteroepitaxial Growth	19
3.4.2	Absorption Coefficient of SiGe Alloys	21
3.4.3	Ge-on-Si IR Photodetectors	21
3.4.4	SiGeC	31
3.4.5	SiGe/Si pin Hetero Bipolar Transistor Integration	32
4	Amplifiers	35
4.1	Preamplifier, Transimpedance Amplifier	35
4.2	Main Amplifier, Limiting Amplifier	36
4.2.1	Limiting Amplifier	37
4.2.2	AGC Amplifier	37

X Contents

5	Integrated Circuit Technology	43
5.1	SiGe Heterojunction Bipolar (HBT)	43
5.2	Deep-Sub-Micron CMOS	45
6	Transimpedance Amplifier Theory	51
6.1	Feedback Theory	51
6.1.1	Shunt-Shunt Feedback	51
6.1.2	Input and Output Resistance	55
6.2	TIA with Ideal Amplifier	57
6.3	TIA with Frequency-Dependent Open-Loop Gain	58
6.3.1	TIA with Folded-Cascode Amplifier Stage	59
6.3.2	TIA with Inverter Amplifier Stages	63
6.3.3	Transimpedance-Gain Switching and Stability of TIA with Inverter Amplifier Stages	70
6.3.4	Three-Stage Burst-Mode TIA with Internal Feedback	76
6.3.5	Transimpedance-Gain Switching and Stability of Three-Stage Burst-Mode TIA with Internal Feedback	79
7	Noise Theory	85
7.1	Sensitivity and Power Penalty	85
7.1.1	Bit-Error Rate	85
7.1.2	Sensitivity	89
7.1.3	Power Penalty	89
7.2	Noise Models of Components	91
7.2.1	Resistor Noise Model	92
7.2.2	Bipolar- and Heterojunction-Bipolar-Transistor Noise Model	93
7.2.3	Field-Effect-Transistor Noise Model	96
7.3	Noise Models of Transimpedance Amplifier	99
7.3.1	Ideal-Amplifier TIA	99
7.3.2	TIA with Bipolar and Heterojunction Bipolar Input Stage	100
7.3.3	TIA with MOS Input Stage	100
7.3.4	Comparison of Bipolar and Field-Effect Transistor Circuits Based on Noise Theory	101
7.4	Noise Models of More Complex TIAs in Deep-Sub-micron CMOS Technology	104
7.4.1	Noise Analysis of Folded-Cascode TIA	104
7.4.2	TIA with CMOS-Inverter Input Circuit	109
8	State of the Art	115
8.1	Silicon Bipolar and BiCMOS Optical Receivers	115
8.2	SiGe Heterojunction Bipolar and SiGe BiCMOS Optical Receivers	121
8.3	Silicon CMOS Optical Receivers	126

8.4	Summary of Results of State-of-the-Art Optical Receivers	135
9	Deep-Sub-μm CMOS Circuits	139
9.1	Simulation Environment and Component Models	139
9.1.1	Simulation Environment	139
9.1.2	Photodiode Model	139
9.1.3	MOSFET Model	141
9.2	Characterization Setup	145
9.3	Designs and Properties of Optical Receivers	146
9.3.1	Folded-Cascode Transimpedance Amplifier	148
9.3.2	Three-Inverter Transimpedance Amplifier	151
9.3.3	Three-Stage Transimpedance Amplifier	154
9.3.4	Three-Stage Burst-Mode Transimpedance Amplifier with Internal Feedback	159
9.3.5	Three-Stage Burst-Mode Transimpedance Amplifier for 2.5 Gb s^{-1}	163
9.3.6	Three-Stage Burst-Mode Transimpedance Amplifier for Ultra-Fast Gain Switching	169
9.4	Summary and Comparison	176
References		183
Index		193